## **Complementary Plastic Silicon Power Transistors**

... designed for low power audio amplifier and low current, high speed switching applications.

Collector-Emitter Sustaining Voltage —

VCEO(sus) = 60 Vdc — MJE171, MJE181

= 80 Vdc — MJE172, MJE182

• DC Current Gain -

 $h_{FE} = 30 \text{ (Min)} @ I_{C} = 0.5 \text{ Adc}$ 

= 12 (Min) @ IC = 1.5 Adc

• Current-Gain — Bandwidth Product —

 $f_T = 50 \text{ MHz (Min)} @ I_C = 100 \text{ mAdc}$ 

Annular Construction for Low Leakages —

ICBO = 100 nA (Max) @ Rated VCB

#### **MAXIMUM RATINGS**

Rating	Symbol	MJE171 MJE181	MJE172 MJE182	Unit
Collector-Base Voltage	V <sub>CB</sub>	80	100	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	60 80		Vdc
Emitter–Base Voltage	V <sub>EB</sub>	7.0		Vdc
Collector Current — Continuous Peak	IC	3.0 6.0		Adc
Base Current	lΒ	1.0		Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	1.5 0.012		Watts W/°C
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	12.5 0.1		Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150		°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	10	°C/W
Thermal Resistance, Junction to Ambient	$\theta$ JA	83.4	°C/W

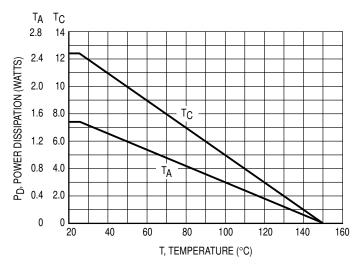


Figure 1. Power Derating

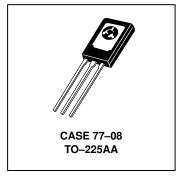
Preferred devices are Motorola recommended choices for future use and best overall value.

#### REV 2

# MJE171\* MJE172\* MJE181\* MJE182\*

\*Motorola Preferred Device

3 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60-80 VOLTS
12.5 WATTS



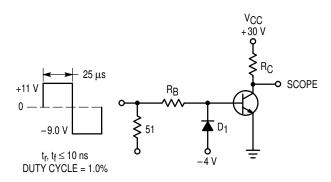


#### **MJE171 MJE172 MJE181 MJE182**

### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		•
Collector–Emitter Sustaining Voltage (IC = 10 mAdc, IB = 0)	MJE171, MJE181 MJE172, MJE182	V <sub>CEO(sus)</sub>	60 80	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0, T <sub>C</sub> = 150 $^{\circ}$ C) (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0, T <sub>C</sub> = 150 $^{\circ}$ C)	MJE171, MJE181 MJE172, MJE182 MJE171, MJE181 MJE172, MJE182	ICBO	_ _ _ _	0.1 0.1 0.1 0.1	μAdc mAdc
Emitter Cutoff Current $(V_{BE} = 7.0 \text{ Vdc}, I_C = 0)$		IEBO	_	0.1	μAdc
ON CHARACTERISTICS					•
DC Current Gain (I <sub>C</sub> = 100 mAdc, $V_{CE}$ = 1.0 Vdc) (I <sub>C</sub> = 500 mAdc, $V_{CE}$ = 1.0 Vdc) (I <sub>C</sub> = 1.5 Adc, $V_{CE}$ = 1.0 Vdc)		hFE	50 30 12	250 — —	_
Collector–Emitter Saturation Voltage ( $I_C = 500 \text{ mAdc}$ , $I_B = 50 \text{ mAdc}$ ) ( $I_C = 1.5 \text{ Adc}$ , $I_B = 150 \text{ mAdc}$ ) ( $I_C = 3.0 \text{ Adc}$ , $I_B = 600 \text{ mAdc}$ )		VCE(sat)	_ _ _	0.3 0.9 1.7	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 1.5 Adc, I <sub>B</sub> = 150 mAdc) (I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 600 mAdc)		V <sub>BE(sat)</sub>	_ _	1.5 2.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 1.0 Vdc)		V <sub>BE(on)</sub>	_	1.2	Vdc
DYNAMIC CHARACTERISTICS					•
Current–Gain — Bandwidth Product (1) (IC = 100 mAdc, VCE = 10 Vdc, f <sub>test</sub> = 10 MHz)		fT	50	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	MJE171/MJE172 MJE181/MJE182	C <sub>ob</sub>	_ 	60 40	pF

<sup>(1)</sup>  $f_T = |h_{fe}| \cdot f_{test}$ 



 $R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  $D_1$  MUST BE FAST RECOVERY TYPE, e.g.:  $1N5825 \ \text{USED ABOVE } I_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW } I_B \approx 100 \ \text{mA} \\ \text{FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES.}$ 

Figure 2. Switching Time Test Circuit

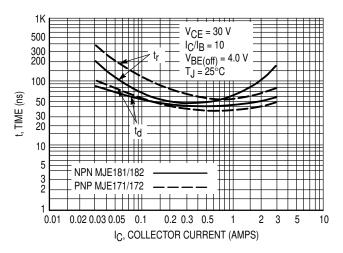


Figure 3. Turn-On Time

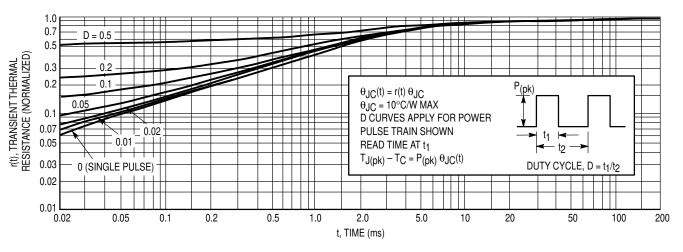


Figure 4. Thermal Response

#### **ACTIVE-REGION SAFE OPERATING AREA**

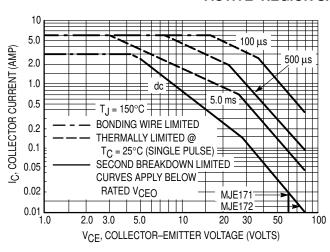


Figure 5. MJE171, MJE172

There are two limitations on the power handling ability of a transistor — average junction temperature and second breakdown. Safe operating area curves indicate  $I_{\hbox{\scriptsize C}}-V_{\hbox{\scriptsize CE}}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 5 and 6 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$ 

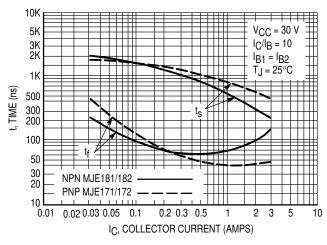


Figure 7. Turn-Off Time

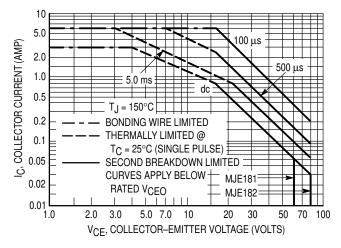


Figure 6. MJE181, MJE182

is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150\,^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperature, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

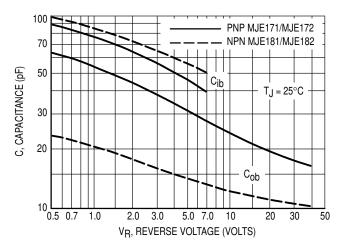
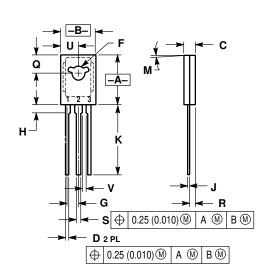


Figure 8. Capacitance

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14 5M 1982
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.425	0.435	10.80	11.04	
В	0.295	0.305	7.50	7.74	
С	0.095	0.105	2.42	2.66	
D	0.020	0.026	0.51	0.66	
F	0.115	0.130	2.93	3.30	
G	0.094	0.094 BSC		BSC	
Н	0.050	0.095	1.27	2.41	
J	0.015	0.025	0.39	0.63	
K	0.575	0.655	14.61	16.63	
M	5° TYP		5° TYP		
Q	0.148	0.158	3.76	4.01	
R	0.045	0.055	1.15	1.39	
S	0.025	0.035	0.64	0.88	
U	0.145	0.155	3.69	3.93	
٧	0.040		1.02		

STYLE 1:

PIN 1. EMITTER
2. COLLECTOR
3. BASE

CASE 77-08 TO-225AA ISSUE V

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